

Electronic Supplementary Information (ESI)

Understanding and improving photoelectrochemical performance of Bi₂O₃/Bi₂S₃ composite

Ji Hyeon Kim,^a Taewan Lim,^a Joon Yong Park,^a Ahyeon Ma,^a Haeun Jung,^a Ha Young Kim,^a Sung Ki Cho^{b,} Hana Yoon,^c and Ki Min Nam^{a,*}*

^a Department of Chemistry and Chemistry Institute for Functional Materials, Pusan National University, Busan 46241, Republic of Korea.

^b Department of Chemical Engineering, Kumoh National Institute of Technology, 61 Daehak-ro, Gumi-si, Gyeongsangbuk-do 39177, Republic of Korea.

^c Korea Institute of Energy Research (KIER), Daejeon 34129, Republic of Korea.

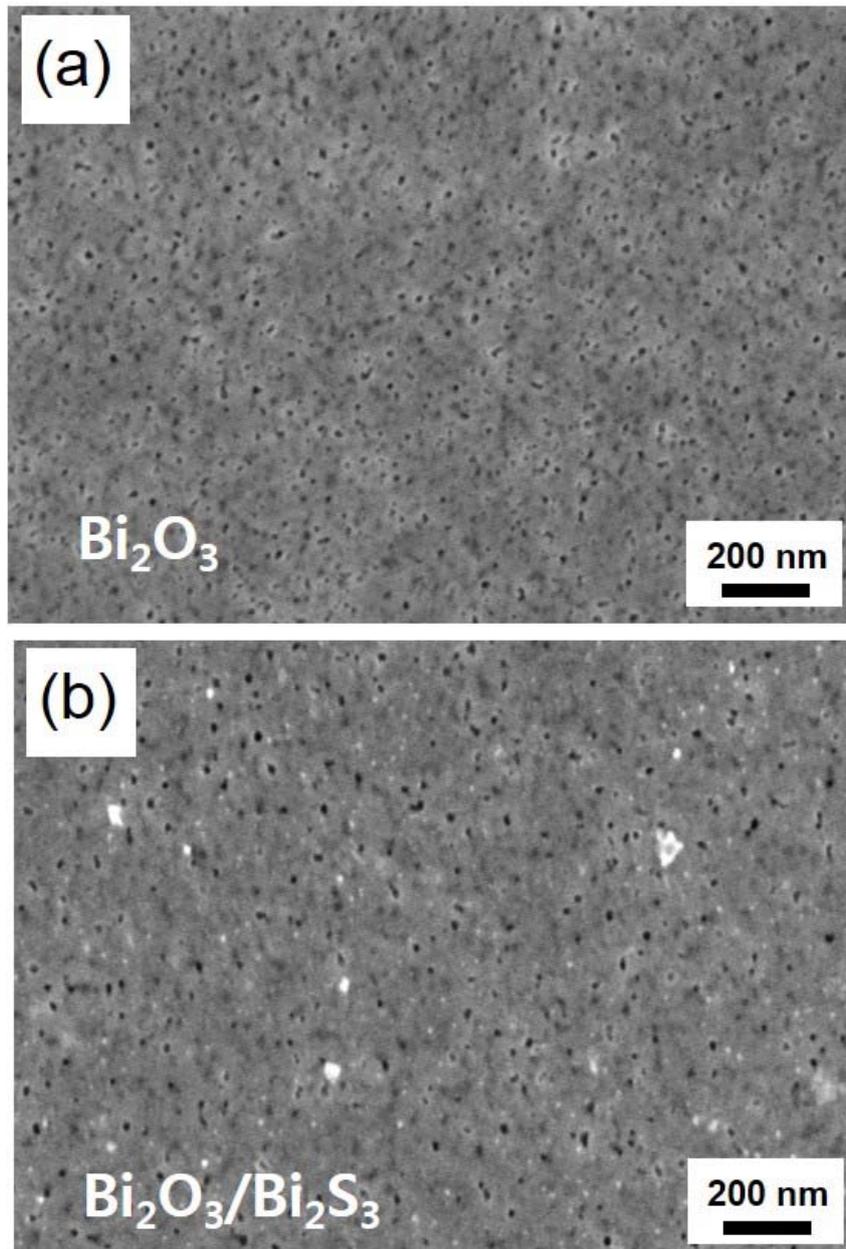


Fig. S1 SEM images of (a) Bi_2O_3 , and (b) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ composite films on the FTO substrate.

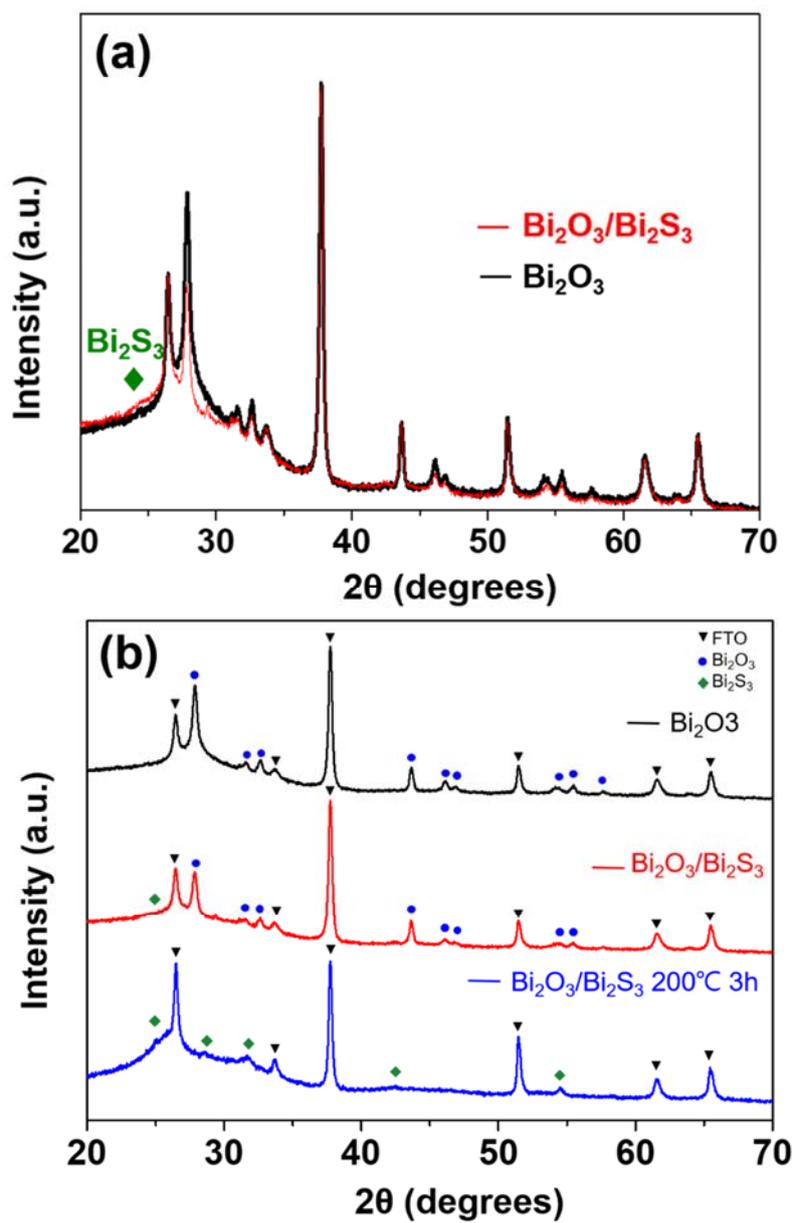


Fig. S2 (a) XRD patterns of Bi₂O₃/Bi₂S₃ (red line), and Bi₂O₃ (black line) films on the FTO substrate. (b) XRD patterns of Bi₂O₃ (black line), Bi₂O₃/Bi₂S₃ before (red line) and after (blue line) annealing process at 200 °C for 3h in air.

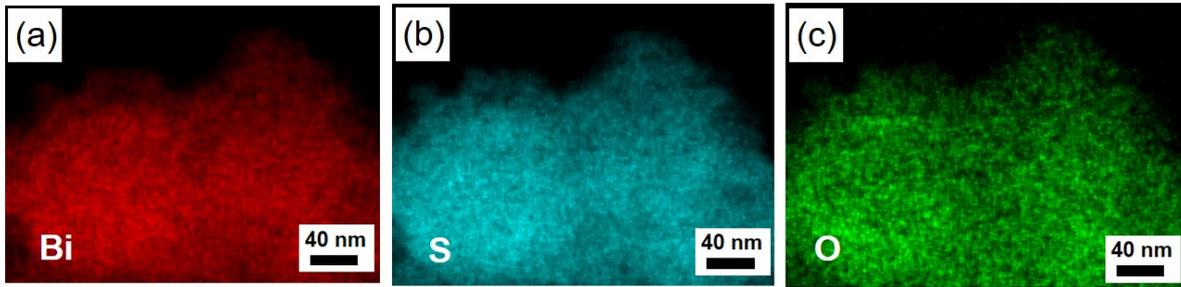


Fig. S3 Element distribution maps of (a) Bi, (b) S, and (c) O on the $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (Sono) composite.

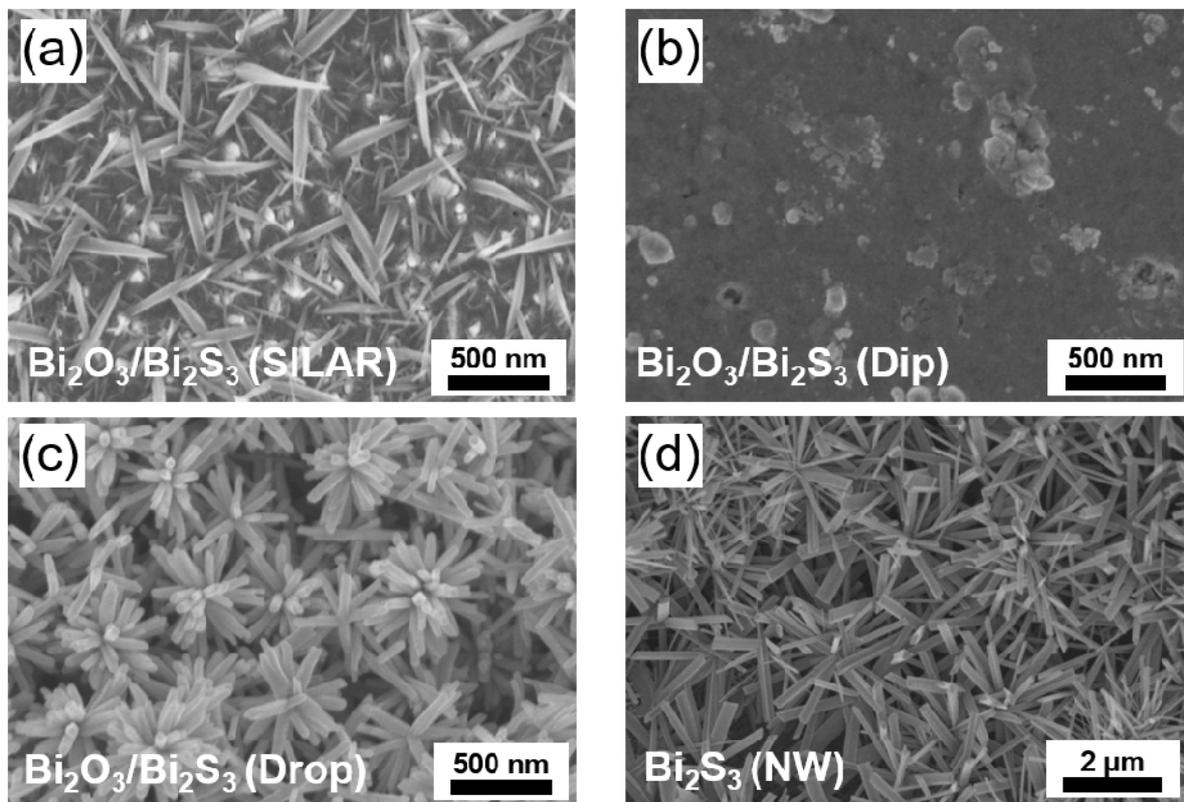


Fig. S4 SEM images of (a) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (SILAR), (b) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (Dip), (c) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (drop), and (d) Bi_2S_3 NW.

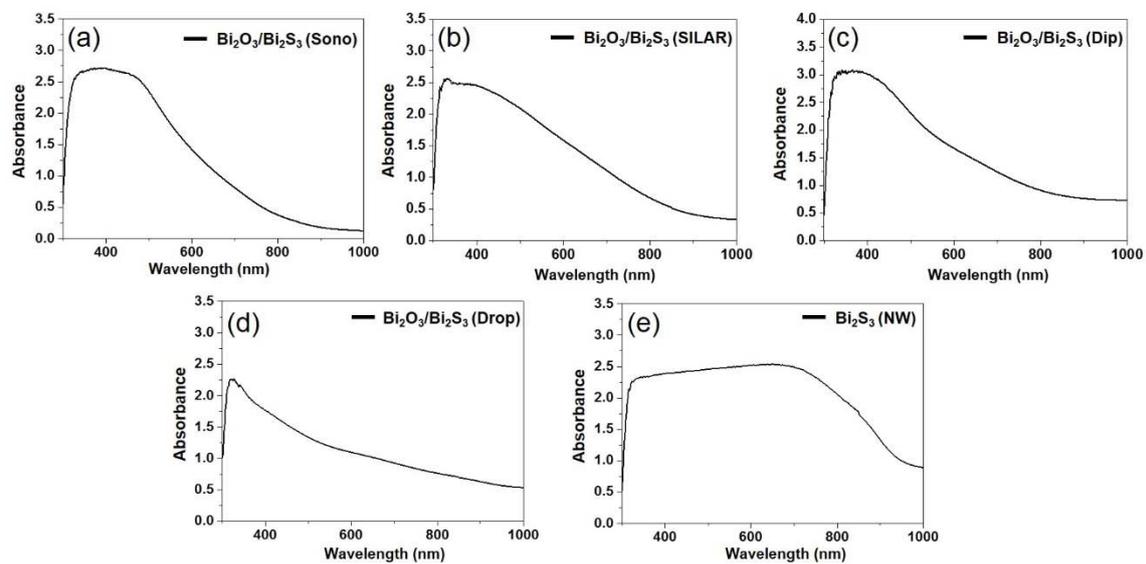


Fig. S5 UV-visible absorption spectrums of (a) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (Sono), (b) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (SILAR), (c) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (Dip), (d) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (drop), and (e) Bi_2S_3 NW.

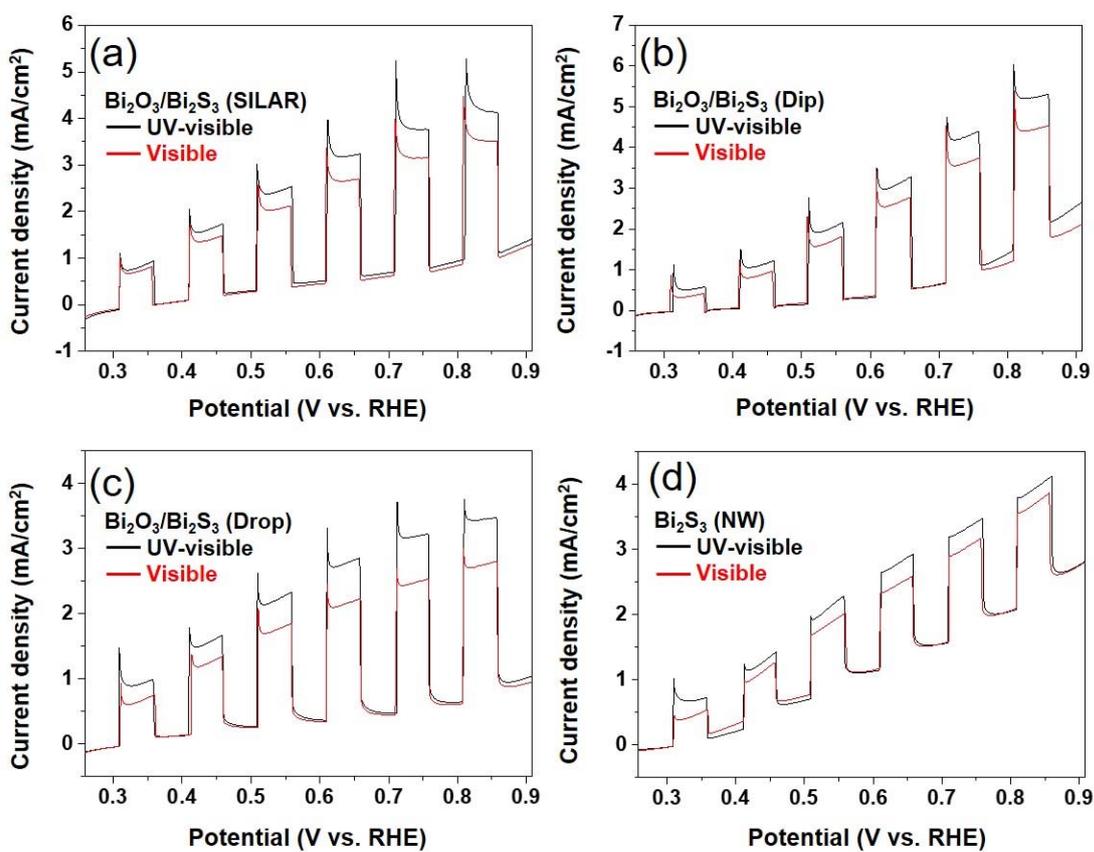


Fig. S6 LSVs of (a) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (SILAR), (b) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (Dip), (c) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (drop), and (d) Bi_2S_3 NW electrodes under UV-visible illumination and visible illumination (> 425 nm) in a 0.1 M Na_2SO_3 and 0.1 M Na_2S solution. Scan rate: 20 mV/s. Light intensity: 100 mW/cm².

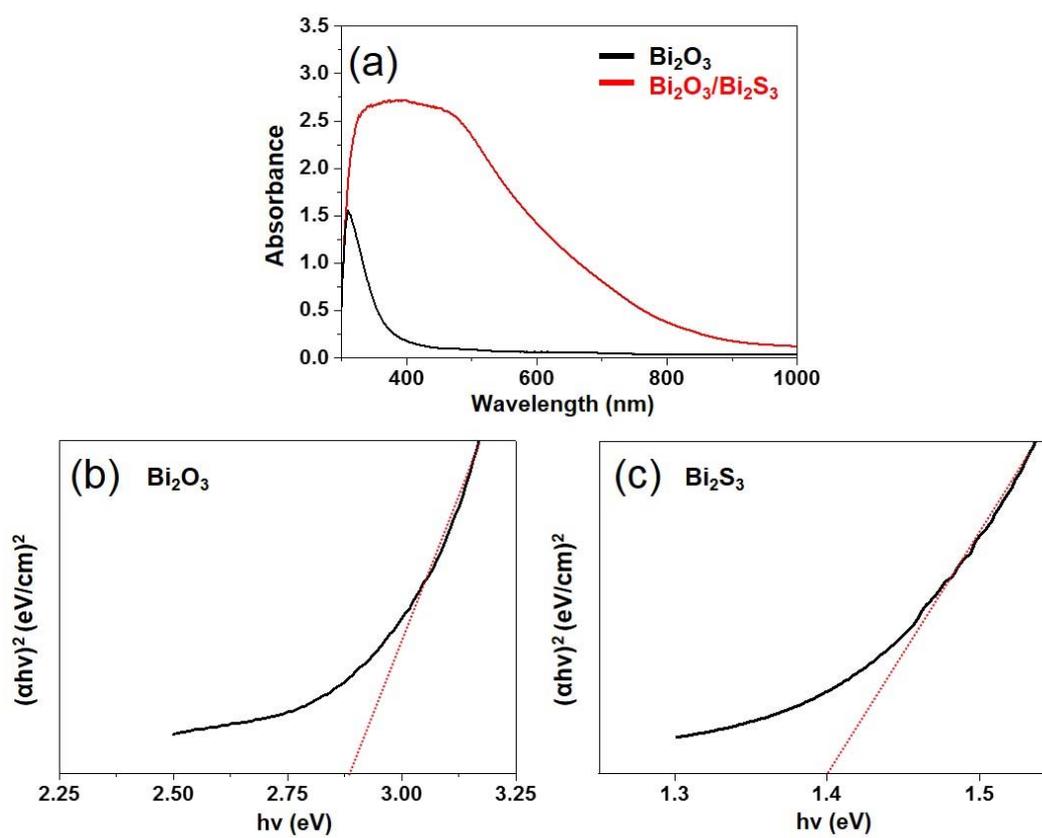


Fig. S7 (a) UV-visible absorption spectra of $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ (red line), and Bi_2O_3 (black line) films. Tauc plots of (b) Bi_2O_3 , and (c) $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3$ electrodes.

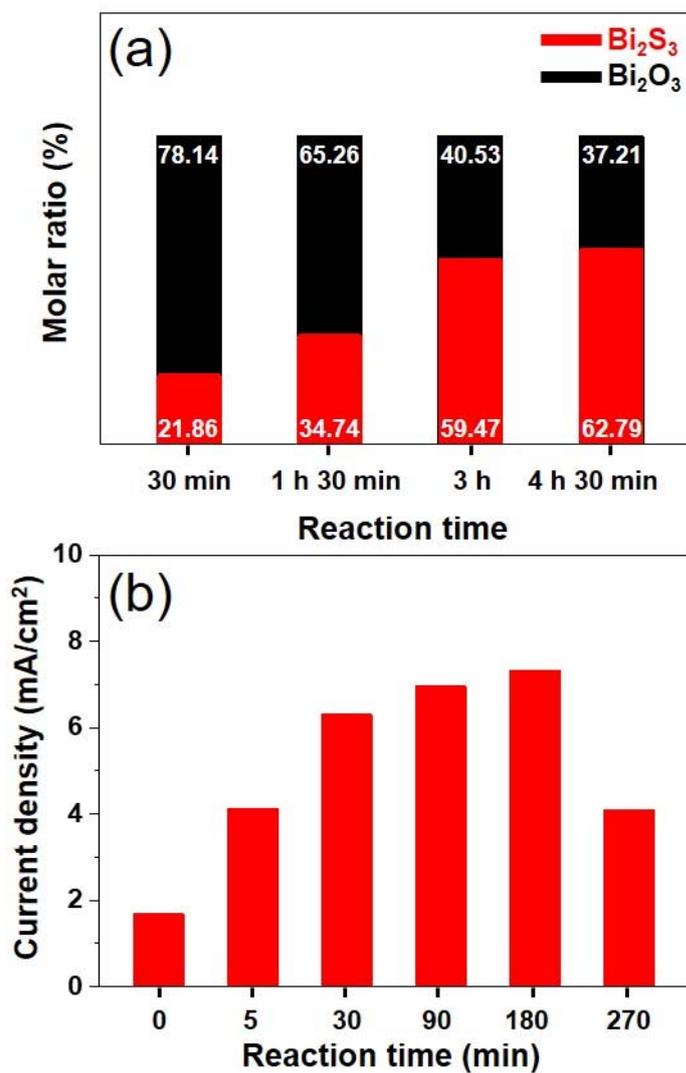


Fig. S8 (a) The Bi₂S₃ to Bi₂O₃ molar ratios measured by the energy-dispersive X-ray (EDX) spectroscopy. (b) Photocurrent density as a function of film thickness and reaction period (Bi₂S₃ loading amount) at 0.75V vs. RHE.

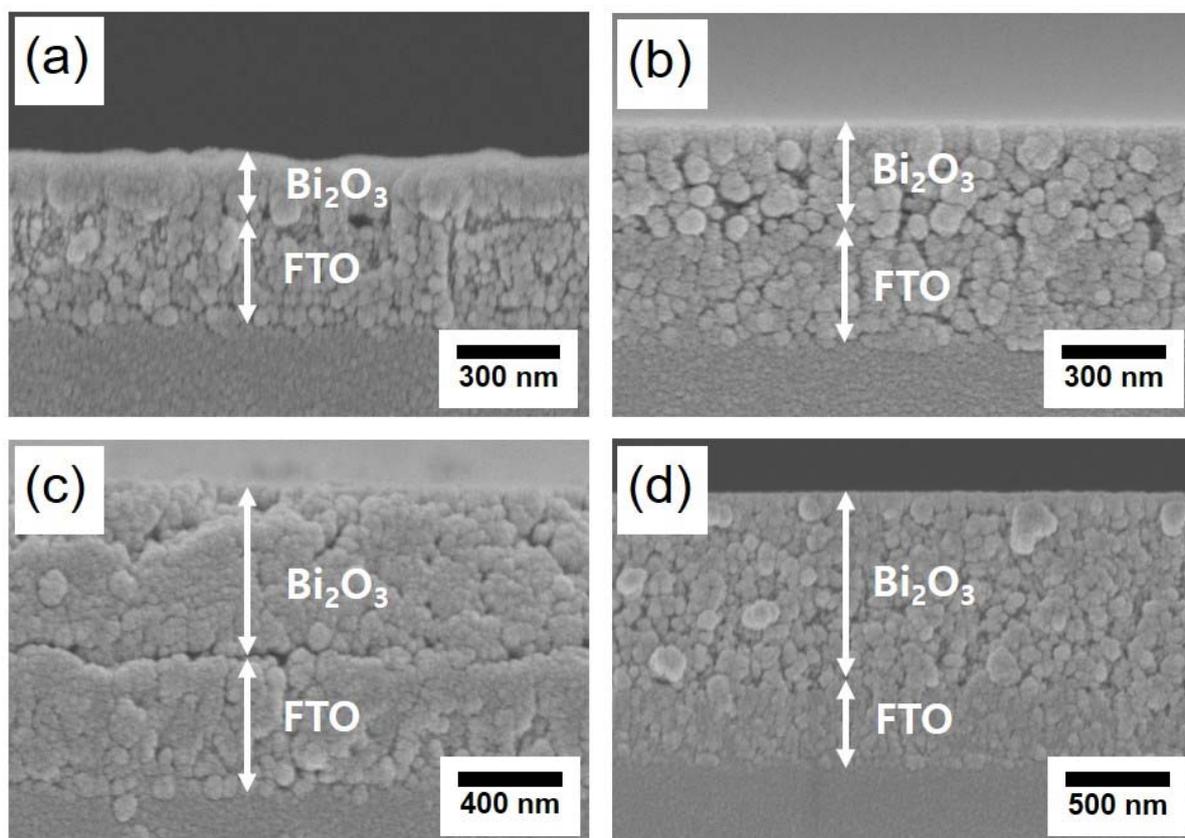


Fig. S9 SEM cross-section images of the $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3(\text{Sono})$ composites depending on the precursor concentrations of (a) 10, (b) 20, (c) 30, and (d) 40 mM.

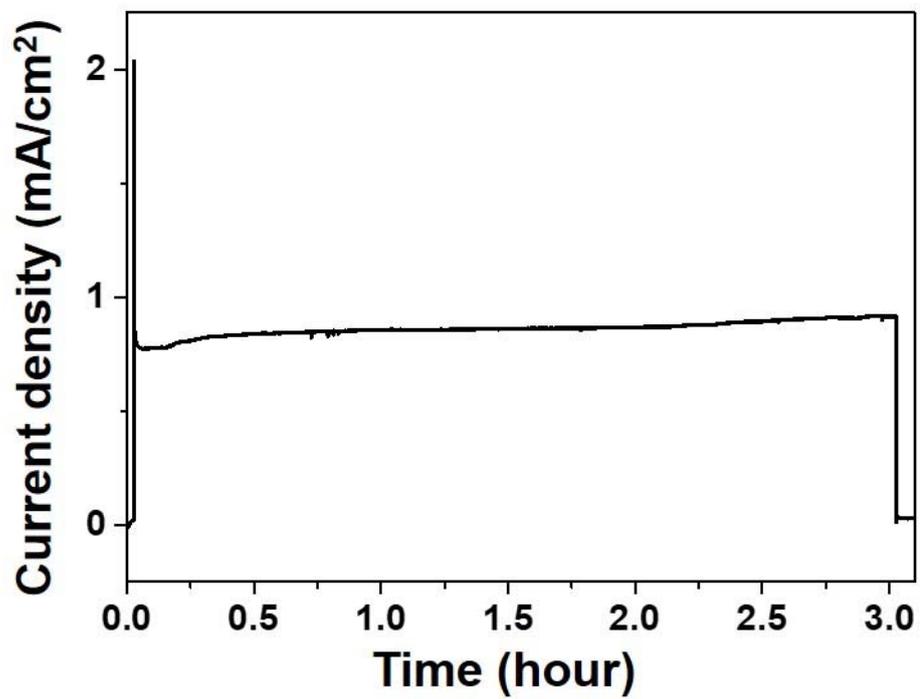


Fig. S10 Current-time response curve of Bi₂O₃/Bi₂S₃(Sono) electrode under UV-visible illumination in 0.4 V vs. RHE in a 0.1 M Na₂SO₃ and 0.1 M Na₂S solution. Light intensity: 100 mW/cm².

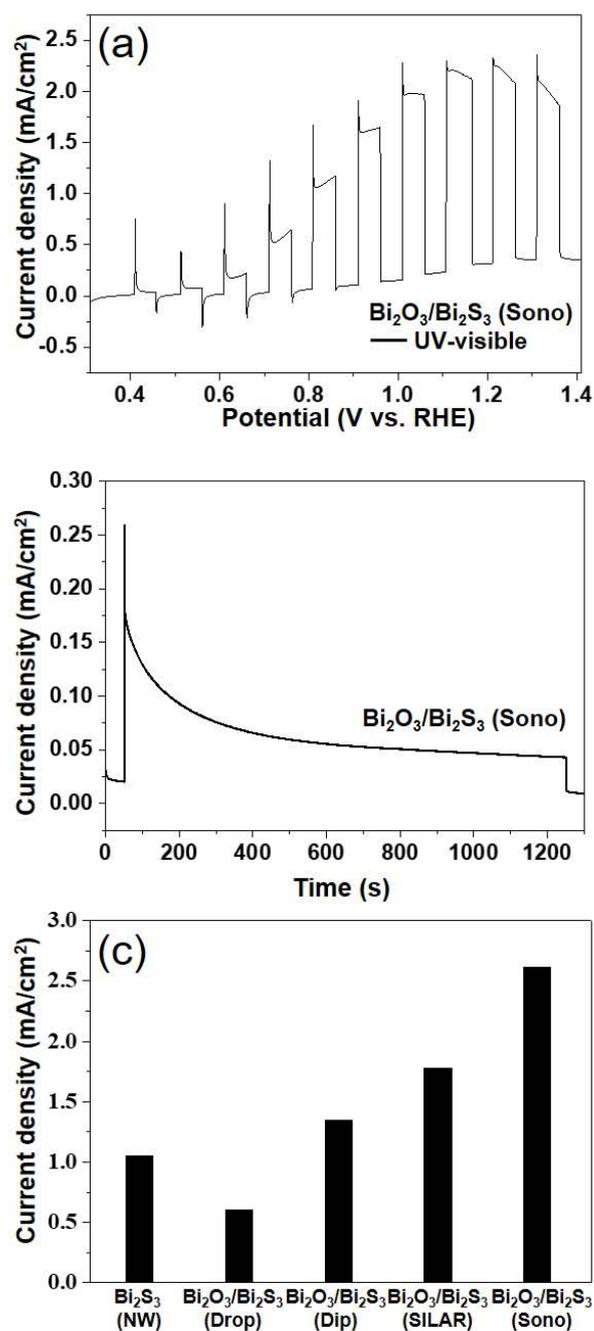


Fig. S11 (a) LSV, and (b) Current-time response curve (0.1 V vs. Ag/AgCl) of Bi₂O₃/Bi₂S₃(Sono) composite under UV-visible illumination in a 0.1 M phosphate buffer (pH 7). Light intensity: 100 mW/cm². (c) Photocurrent density of electrodes under UV-visible illumination at an applied potential of 1.2 V vs. RHE in a 0.1 M phosphate buffer (pH 7).

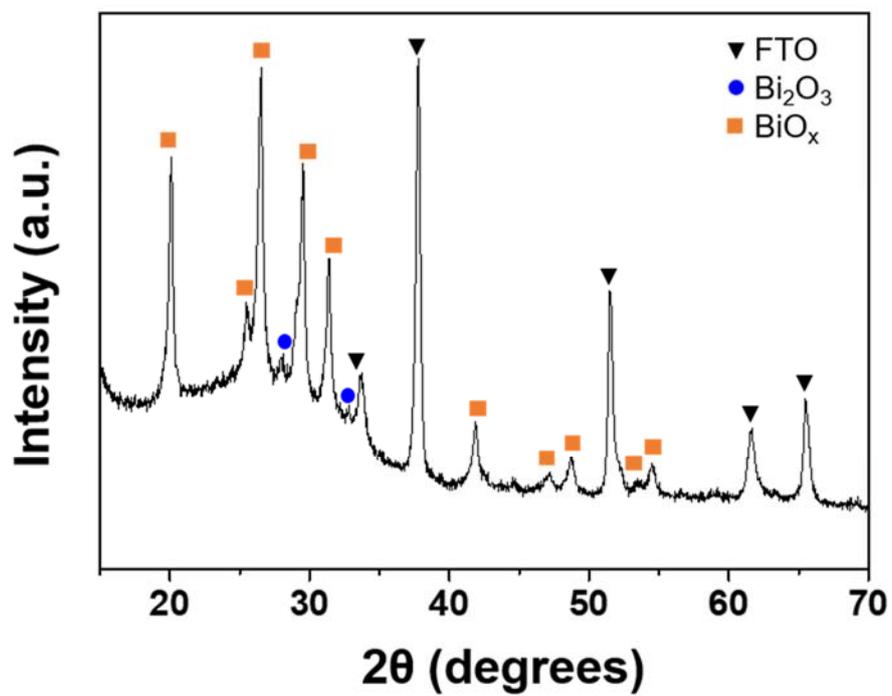


Fig. S12 XRD patterns of Bi₂O₃/Bi₂S₃(Sono) composite after water oxidation indicating that the decomposition of Bi₂S₃ in the solution.

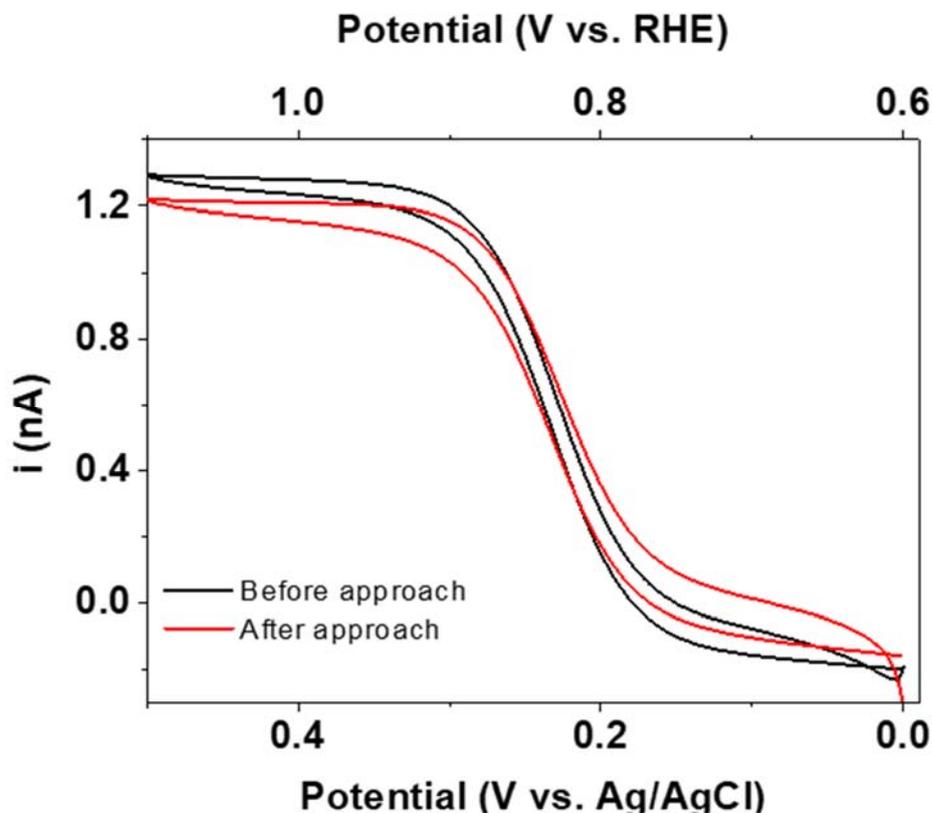


Fig. S13 Cyclic voltammograms of Pt UME tip measured in 1 mM ferrocene methanol ($D = 6.7 \times 10^{-6} \text{ cm}^2/\text{s}$)/0.1 M Na_2SO_4 solution before and after approach to the substrate. Assuming that $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3(\text{Sono})$ substrate is almost insulating at the open circuit under dark, the normalized current (I_T) for the negative feedback $\text{Bi}_2\text{O}_3/\text{Bi}_2\text{S}_3(\text{Sono})$ substrate can be defined as:[1]

$$I_T(L) = \frac{i_T}{i_{T,\infty}} = \left[0.292 + \frac{1.515}{(d/a)} + 0.6553 \exp(-2.4035/(d/a)) \right]^{-1}$$

where i_T and $i_{T,\infty}$ are the steady-state tip current when the tip is close to the substrate, and far from the substrate, respectively, and d is distance from substrate. For cyclic voltammogram, the measured i_T and $i_{T,\infty}$ were $1.2 \times 10^{-9} \text{ A}$ and $1.3 \times 10^{-9} \text{ A}$, respectively. Consequently, d is obtained as $15 \text{ }\mu\text{m}$ according to the above equation.

[1] A. J. Bard, L. R. Faulkner, John Wiley & Sons, Inc., (2001) 34.